

REMARKS

With the present amendment, originally filed claims 1-66 have been canceled and replaced with new claims 67-124. The new claims find support throughout the original disclosure, as indicated in the following table:

CLAIM(S)	CLAIM ELEMENT (PREVIOUSLY RECITED ELEMENTS NOT INCLUDED)	LOCATION OF SUPPORT
67	R^1, R^2, R^3 and R^4 are independently selected from the group consisting of substituents having a terminal $-CR^7R^8R^9$ group.	Paragraph 41, structure (II); claim 1 as filed
67, 86-88	R^7 is hydrogen, alkyl, or fluoroalkyl, R^8 is fluoroalkyl, and R^9 is OH, COOH or an acid-cleavable moiety.	Paragraph 41; claim 1 as filed.
68	R^1, R^2, R^3 and R^4 are independently selected from the group consisting of substituents having the structure $-(Q)_n-CR^7R^8R^9$ wherein n is zero or 1.	Paragraph 41; structures (II) and (III); claim 36 as filed (regarding the definition of n as zero or 1).
69	Q is selected from the group consisting of substituted and unsubstituted arylene, substituted and unsubstituted cycloalkylene, and C_1 - C_4 alkylene optionally substituted with at least one nonhydrogen substituent selected from alkyl and fluoroalkyl.	Paragraph 41; claim 1 as filed.
70	Q is fluorinated.	Paragraph 19 (page 7, last line - page 8, line 1).
71-73, 75-78, 80, 81	Q is selected from the group consisting of arylene, fluorinated arylene, cycloalkylene, fluorinated cycloalkylene, and C_1 - C_4 alkylene optionally substituted with 1-8 nonhydrogen substituents selected from alkyl and fluoroalkyl.	Paragraph 42; paragraph 19 (page 7, last line - page 8, line 1).
74	Q is bicyclic.	Lower right structure on page 19; upper left structure on page 20.
79	Q is C_1 - C_4 alkylene optionally substituted with 1-8 nonhydrogen substituents selected from alkyl and fluoroalkyl.	Text accompanying structure (III), throughout.
82	R^7 is hydrogen, C_1 - C_6 alkyl, or C_1 - C_6 fluoroalkyl.	Paragraph 43.
83-85	R^7 is hydrogen, C_1 - C_6 alkyl, trifluoromethyl, or trifluoromethyl-substituted C_1 - C_6 alkyl.	Paragraph 43.
89, 90	R^9 is an acid-cleavable ester, ether or carbonate.	Paragraph 45.

CLAIM(S)	CLAIM ELEMENT (PREVIOUSLY RECITED ELEMENTS NOT INCLUDED)	LOCATION OF SUPPORT
91-93	R ⁹ has the formula -(L) _v -(CO)-OR ¹⁴ wherein v is zero or 1, L is a linking group, and R ¹⁴ is selected from the group consisting of tertiary alkyl moieties, cyclic or alicyclic substituents with a tertiary attachment point, and 2-trialkylsilylethyl moieties.	Paragraph 45.
94	R ¹⁴ is a cyclic or alicyclic substituent with a tertiary attachment point.	Paragraph 45.
95-97	R ¹⁴ is selected from the group consisting of adamantyl, norbornyl, isobornyl, 2-methyl-2-adamantyl, 2-methyl-2-isobornyl, 2-butyl-2-adamantyl, 2-propyl-2-isobornyl, 2-methyl-2-tetracyclododecenyl, 2-methyl-2-dihydro-dicyclopentadienyl-cyclohexyl, 1-methylcyclopentyl, 1-methylcyclohexyl, 2-trimethylsilylethyl, and 2-triethylsilylethyl.	Paragraph 45.
98	Polymer includes additional monomer units of structural formula (IV).	Paragraph 49; claim 13 as filed.
99, 100	At least one of R ¹⁰ , R ¹¹ , R ¹² and R ¹³ is selected from the group consisting of acid-cleavable esters, ethers, and carbonates.	Claims 13, 15, and 16 as filed.
101, 102	Lithographic photoresist compositions comprising a polymer of the invention and a radiation-sensitive acid generator.	Paragraph 56; claims 36 and 37 as filed.
103, 104	The composition is a positive resist and further includes a dissolution inhibitor.	Paragraph 57.
105, 106	The composition is a negative resist and further includes a crosslinking agent.	Paragraph 60.
107-110	Glycoluril crosslinking agents.	Paragraph 61 (pages 28-29); claims 43 and 44 as filed.
111, 115	Process for generating a resist image on a substrate.	Paragraphs 69-74; claims 45 and 46 as filed.
112, 116	Radiation has a wavelength less than 250 nm.	Paragraph 24; claims 47 and 48 as filed.
113, 117	Radiation is 157 nm.	Paragraphs 24 and 71; claims 49 and 50 as filed.
114, 118	Substrate is a bilayer.	Paragraph 69; claims 51 and 52 as filed.
119, 121	Method of forming a patterned material structure on a substrate using a positive resist.	Paragraphs 69-74; claims 53 and 54 as filed.

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120, 122	The method employs deep ultraviolet radiation.	Paragraph 24.
123-124	Method of forming a patterned material structure on a substrate using a negative resist.	Paragraphs 69-74; claim 62 as filed.

Note that the sections cited as providing support for the various claim elements are not necessarily inclusive of all possible sections that provide support for a particular claim element.

The specification has also been amended, throughout, to correct minor and inadvertent typographical, grammatical, and spelling errors in the application as filed. The only substantive changes that have been made serve to conform certain sections of the specification to other sections present in the originally filed specification and claims.

As all amendments and new claims are fully supported by the original disclosure, no new matter has been added, and entry of all amendments and new claims is thus proper.

Should the Examiner have any questions concerning this communication, please contact the undersigned attorney at (650) 330-0900.

Respectfully submitted,

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